

## Description

### Product Summary

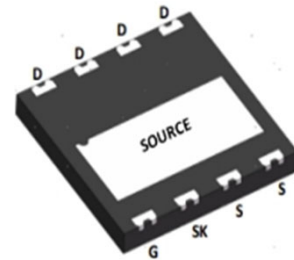
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)(Typ)$	$I_D(A)$
700	240	6.7

## Feature

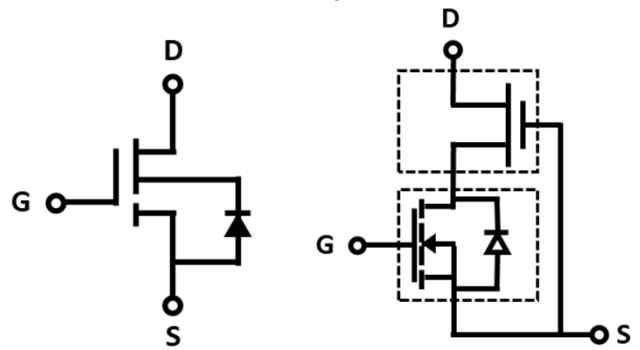
- Easy to use, compatible with standard gate drivers
- Excellent  $Q_G \times R_{DS(on)}$  figure of merit (FOM)
- Low  $Q_{RR}$ , no free-wheeling diode required
- Low switching loss
- RoHS compliant and Halogen-free

## Applications

- High efficiency power supplies
- Telecom and datacom
- Automotive
- Servo motors



**DFN8080-8L (Bottom View)**



**Schematic Symbol**

**Cascode Device Structure**

## Absolute maximum rating@25°C

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		$V_{DS}$	700	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Transient Drain-Source Voltage <sup>1)</sup>		$V_{TDS}$	800	V
Continuous Drain Current	$T_C=25^\circ C$	$I_D$	6.7	A
	$T_C=100^\circ C$		4.2	
Pulsed Drain Current (Pulse Width: 100μs)	$T_C=25^\circ C$	$I_{DM}$	23	A
	$T_C=150^\circ C$		17	
Power Dissipation		$P_D$	21	W
Soldering Peak Temperature		$T_{CSOLD}$	260	°C
Operating Junction and Storage Temperature		$T_J, T_{STG}$	-55 to 150	°C

## Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	-	6.1	-	°C/W
Thermal Resistance, Junction-to-Ambient <sup>2)</sup>	$R_{\theta JA}$	-	50	-	°C/W

## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Units
Statistic Characteristics							
Maximum Drain-Source Voltage	V <sub>DS-Max</sub>	V <sub>GS</sub> = 0V		700	-	-	V
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA		-	1000	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =700V, V <sub>GS</sub> =0V	T <sub>J</sub> =25°C	-	7	20	μA
			T <sub>J</sub> =150°C	-	50	-	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V		-	-	±150	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 500μA		3	4	5	V
Drain-Source On-State Resistance <sup>3)</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> =12V, I <sub>D</sub> =4A	T <sub>J</sub> =25°C	-	240	300	mΩ
			T <sub>J</sub> =150°C	-	480	-	
Dynamic Characteristics							
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 400V, V <sub>GS</sub> = 0V, f = 1MHz		-	320	-	pF
Output Capacitance	C <sub>OSS</sub>			-	17	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	0.6	-	
Effective Output Capacitance, Energy Related	C <sub>o(er)</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0-400V		-	26	-	pF
Effective Output Capacitance, Time Related	C <sub>o(tr)</sub>			-	70	-	
Output Charge	Q <sub>OSS</sub>			-	28	-	nC
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = 400V, I <sub>D</sub> = 3A, V <sub>GS</sub> =0-12V, R <sub>G</sub> =47Ω		-	36	-	ns
Turn-on Rise Time	t <sub>r</sub>			-	16	-	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	40	-	
Turn-Off Fall Time	t <sub>f</sub>			-	8	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 400V, I <sub>D</sub> = 4A, V <sub>GS</sub> =0-12V		-	7	-	nC
Gate-Source Charge	Q <sub>gs</sub>			-	2	-	
Gate-Drain Charge	Q <sub>gd</sub>			-	2.6	-	
Reverse Diode Characteristics							
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =2A		-	1.2	-	V
		V <sub>GS</sub> =0V, I <sub>S</sub> =4A	T <sub>J</sub> =25°C	-	1.6	-	
			T <sub>J</sub> =150°C	-	2.3	-	
Reverse Recovery Time	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =4A, V <sub>DD</sub> =400V, di/dt=1000A/μs		-	16	-	ns
Reverse Recovery Charge	Q <sub>rr</sub>			-	28	-	μC

## Notes:

- Off-state spike duty cycle < 0.01, spike duration < 2 $\mu s$
- Device on one layer epoxy PCB for drain connection (vertical and without air stream cooling, with 6cm<sup>2</sup>copper area and 70 $\mu m$  thickness)
- Dynamic on-resistance; see Figure 19 and 20 for test circuit and configurations

## Typical Characteristics

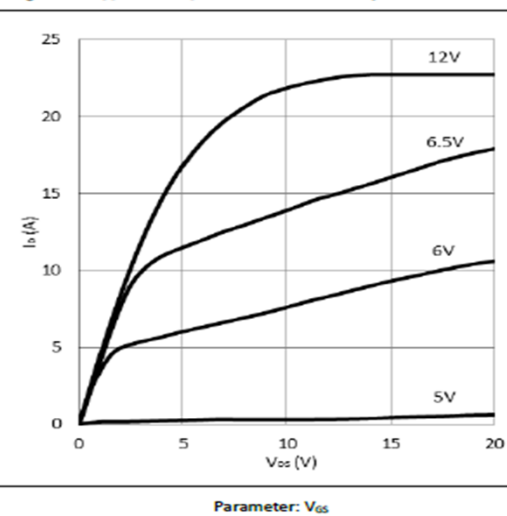
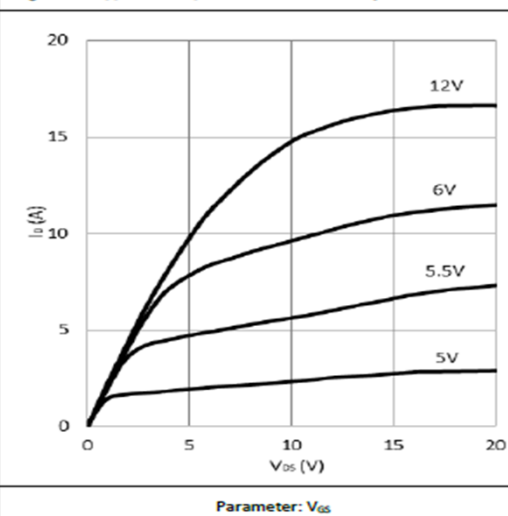
Figure 1. Typical Output Characteristics  $T_J=25^\circ\text{C}$ Figure 2. Typical Output Characteristics  $T_J=150^\circ\text{C}$ 

Figure 3. Typical Transfer Characteristics

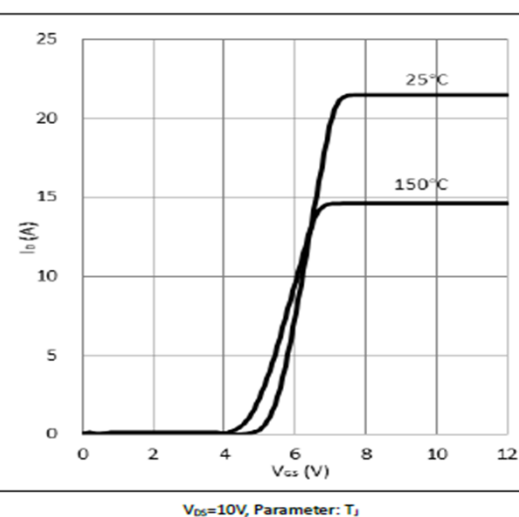
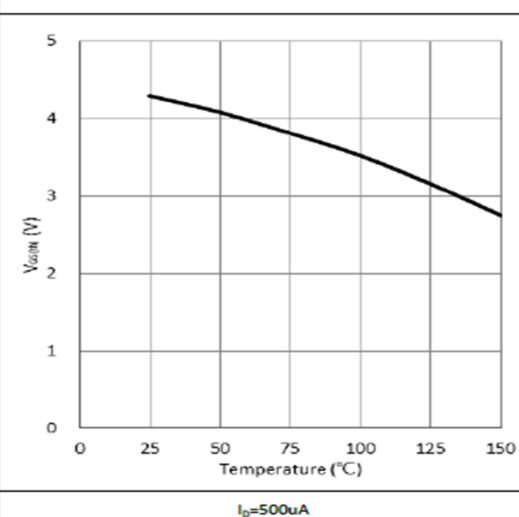
Figure 4.  $V_{DS(on)}$  Vs Temperature Characteristics

Figure 5. Normalized On-resistance

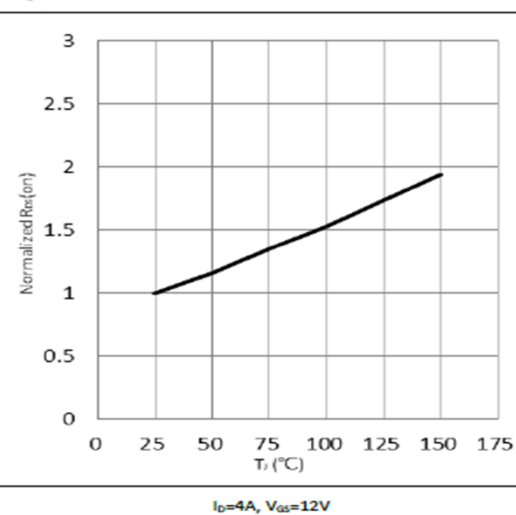


Figure 6. Typical Capacitance

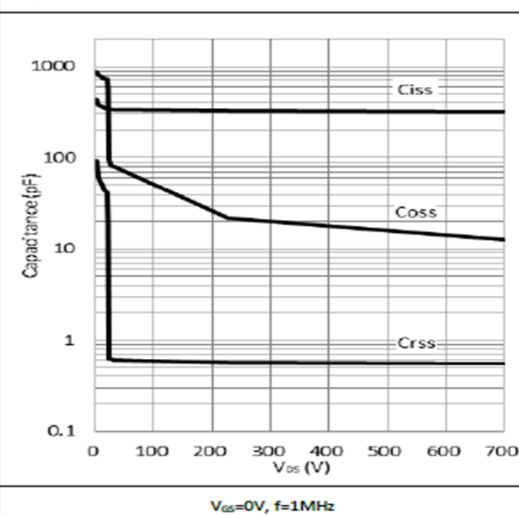


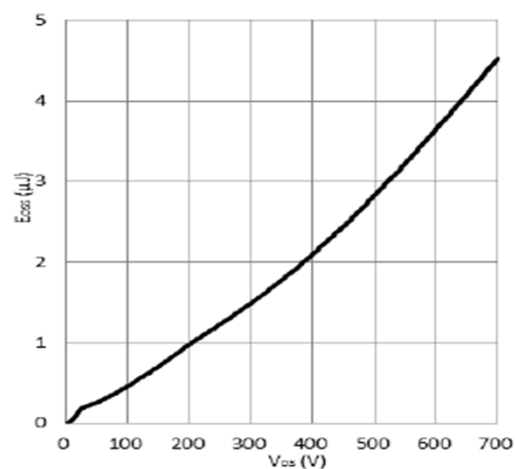
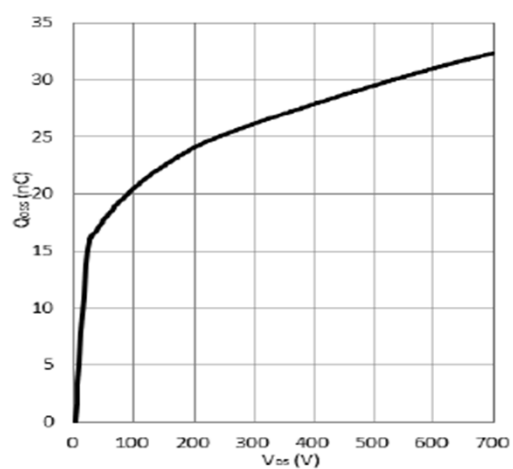
Figure 7. Typical  $C_{oss}$  Stored Energy $V_{gs}=0V, f=1MHz$ Figure 8. Typical  $Q_{oss}$  $V_{gs}=0V, f=1MHz$ 

Figure 9. Forward Characteristic of Rev. Diode

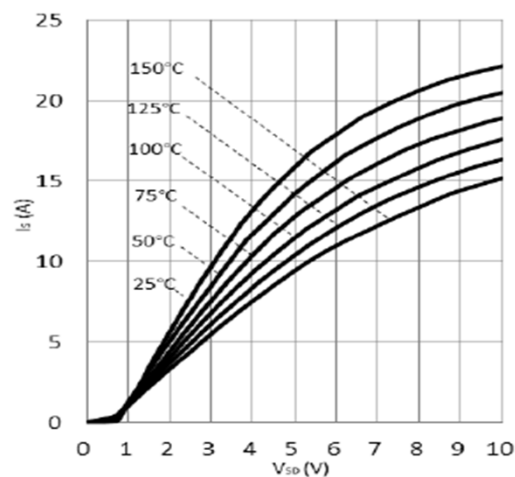
 $I_S=f(V_{SD}), \text{Parameter } T_J$ 

Figure 10. Typical Gate Charge

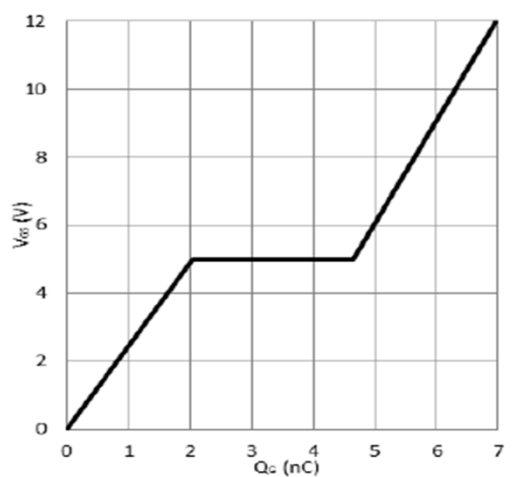
 $I_{DS}=4A, V_{DS}=400V$ 

Figure 11. Power Dissipation

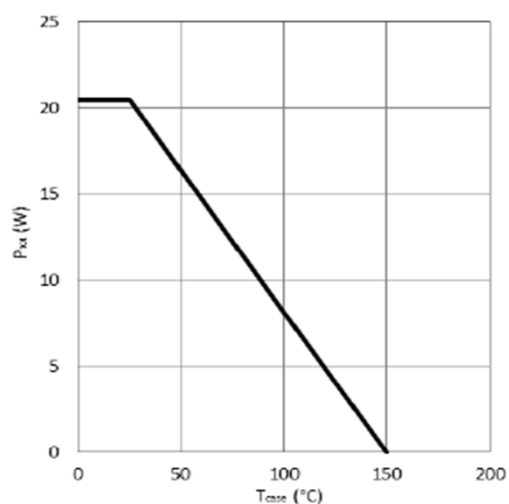


Figure 12. Current Derating

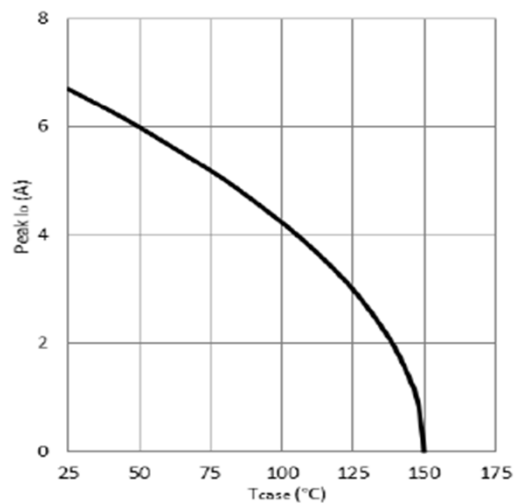


Figure 13. Transient Thermal Resistance

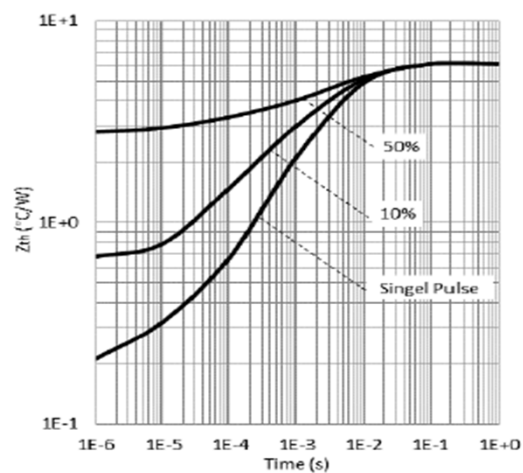
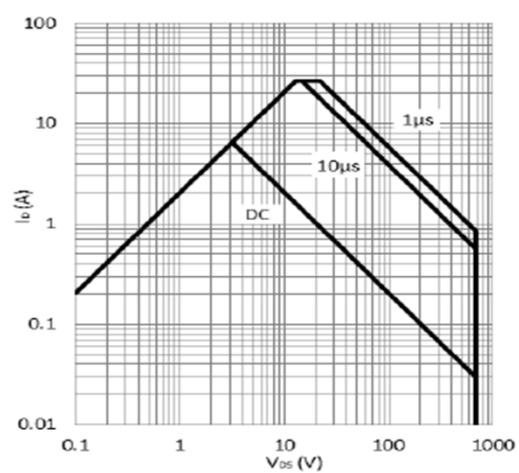
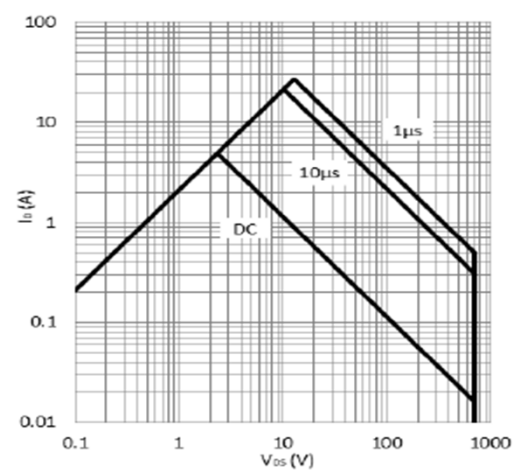


Figure 14. Safe Operating Area  $T_c=25^\circ\text{C}$



calculated based on thermal limit

Figure 15. Safe Operating Area  $T_c=80^\circ\text{C}$



calculated based on thermal limit

## Test Circuits and Waveforms

Figure 16. Switching Time Test Circuit

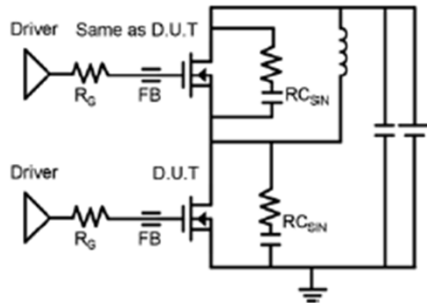


Figure 17. Switching Time Waveform

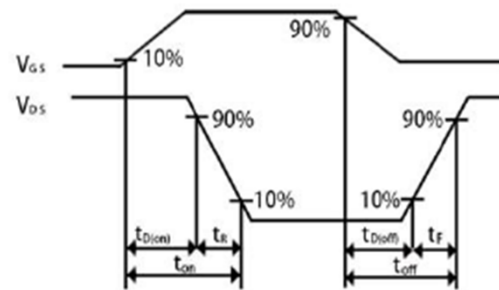


Figure 18. Dynamic  $R_{DS(on)}$  Test Circuit

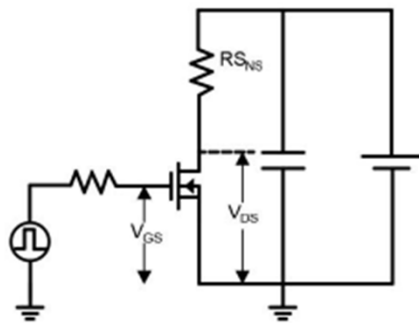


Figure 19. Dynamic  $R_{DS(on)}$  Waveform

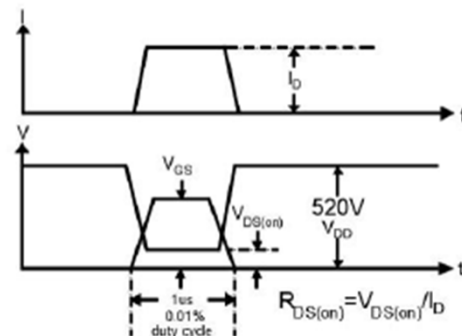


Figure 20. Diode Characteristic Test Circuits

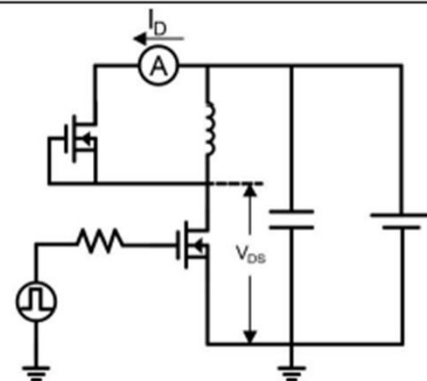
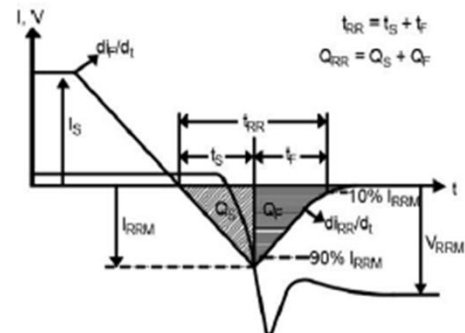
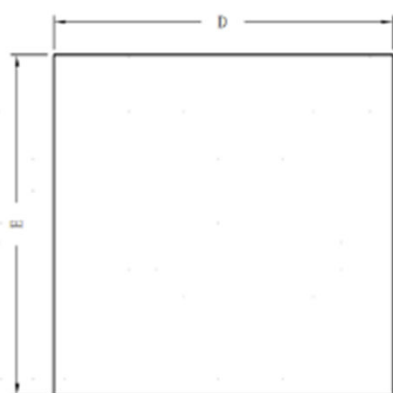


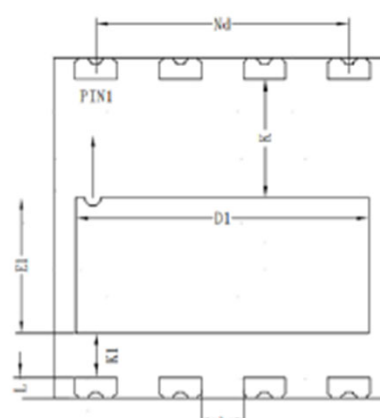
Figure 21. Diode Recovery Waveform



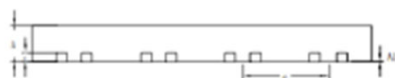
## Product Dimension (DFN8080-8L)



TOP VIEW




BOTTOM VIEW



SIDE VIEW

SYMBOL	Millimeter		
	Min	Nom	Max
A	0.80	0.90	1.15
A1	0	0.02	0.05
c	—	0.20	—
b	0.90	1.00	1.10
D	7.90	8.00	8.10
D1	6.85	6.95	7.05
E	7.90	8.00	8.10
E1	3.10	3.20	3.30
e	2.00BSC		
Nd	6.00BSC		
K	2.70	2.80	2.90
K1	0.90	1.00	1.10
L	0.40	0.50	0.60


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